

**SKHI 21A ...****SEMDRIVER™****Hybrid Dual MOSFET Driver****SKHI 21A**

Preliminary Data

**Features**

- drives MOSFETs with  $V_{DS(on)} < 10 \text{ V}$
- is compatible to old SKHI 21
- CMOS compatible inputs
- Short circuit protection by  $V_{CE}$  monitoring and switch off
- Drive interlock top / bottom
- Isolation by transformers
- Supply undervoltage protection (13 V)
- Error latch / output

**Typical Applications**

- Driver for MOSFET modules in bridge circuits in choppers, inverter drives, UPS and welding inverters

1) see fig. 6

2) At  $R_{CE} = 18 \text{ k}\Omega$ ,  $C_{CE} = 330 \text{ pF}$ **Absolute Maximum Ratings**

<b>Symbol</b>	<b>Conditions</b>	<b>Values</b>	<b>Units</b>
$V_S$	Supply voltage prim.	18	V
$V_{iH}$	Input signal volt. (High)	$V_S + 0,3$	V
$I_{out,PEAK}$	Output peak current	8	A
$I_{out,AVmax}$	Output average current	40	mA
$f_{max}$	max. switching frequency	50	kHz
$V_{CE}$	Collector emitter voltage sense across the IGBT	1200	V
$dv/dt$	Rate of rise and fall of voltage secondary to primary side	50	kV/μs
$V_{isolIO}$	Isolation test voltage input - output (2 sec. AC)	2500	Vac
$V_{isol12}$	Isolation test voltage output 1 - output 2 (2 sec. AC)	1500	V
$R_{Gonmin}$	Minimum rating for $R_{Gon}$	3	Ω
$R_{Goffmin}$	Minimum rating for $R_{Goff}$	3	Ω
$Q_{out/pulse}$	Max. rating for output charge per pulse	4 <sup>1)</sup>	μC
$T_{op}$	Operating temperature	- 40 ... + 85	°C
$T_{stg}$	Storage temperature	- 40 ... + 85	°C

**Characteristics** $T_a = 25 \text{ °C}$ , unless otherwise specified

<b>Symbol</b>	<b>Conditions</b>	<b>min.</b>	<b>typ.</b>	<b>max.</b>	<b>Units</b>
$V_S$	Supply voltage primary side	14,4	15	15,6	V
$I_{SO}$	Supply current primary side (no load)		80		mA
	Supply current primary side (max.)			290	mA
$V_i$	Input signal voltage on/off		15 / 0		V
$V_{iT+}$	Input threshold voltage (High)	10,9	11,7	12,5	V
$V_{iT-}$	Input threshold voltage (Low)	4,7	5,5	6,5	V
$R_{in}$	Input resistance		10		kΩ
$V_{G(on)}$	Turn on gate voltage output		+ 15		V
$V_{G(off)}$	Turn off gate voltage output		0		V
$R_{GE}$	Internal gate-emitter resistance		22		kΩ
$f_{ASIC}$	Asic system switching frequency		8		MHz
$t_{d(on)IO}$	Input-output turn-on propagation time	0,85	1	1,15	μs
$t_{d(off)IO}$	Input-output turn-off propagation time	0,85	1	1,15	μs
$t_{d(terr)}$	Error input-output propagation time		0,6		μs
$t_{pERRRESET}$	Error reset time		9		μs
$t_{TD}$	Top-Bot Interlock Dead Time	3,3		4,3	μs
$V_{CEsat}$	Reference voltage for $V_{CE}$ -monitoring		5 <sup>2)</sup>	10	V
$C_{ps}$	Coupling capacitance primary secondary		12		pF
$MTBF$	Mean Time Between Failure $T_a = 40^\circ\text{C}$		2,0		$10^6 \text{ h}$
$w$	weight		45		g

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